



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _C = +25°C
80V	16mΩ @ V _{GS} = 10V	35A
00 V	22mΩ @ V _{GS} = 6V	30A

Description and Applications

This MOSFET has been designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

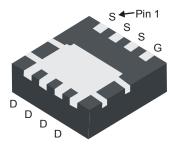
- · Synchronous Rectifier
- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

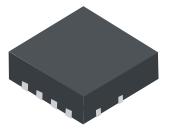
- Low R_{DS(ON)} ensures on state losses are minimized
- Excellent Q_{gd x} R_{DS(ON)} Product (FOM)
- Advanced Technology for DC/DC converts
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- 100% UIS (Avalanche) rated
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

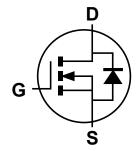
- Case: POWERDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe.
 Solderable per MIL-STD-202, Method 208 <a>®3
- Weight: 0.008 grams (approximate)







Top View



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging		
DMT8012LFG-7	POWERDI3333-8	2,000/Tape & Reel		
DMT8012LFG-13	POWERDI3333-8	3,000/Tape & Reel		

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



SG8 = Product Type Marking Code YYWW = Date Code Marking YY = Last digit of year (ex: 13 = 2013) WW = Week code (01 ~ 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage		V _{DSS}	80	V
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current (Note 5) \/ - = 10\/	T _A = +25°C T _A = +70°C	I _D	9.5 7.6	А
Continuous Drain Current (Note 5) V _{GS} = 10V	$T_C = +25$ °C $T_C = +70$ °C	I _D	35 28	А
Maximum Continuous Body Diode Forward Current (Note 5)		I _S	2	Α
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	80	Α	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Total Dower Dissination (Note 5)	T _A = +25°C	6	2.2	W	
Total Power Dissipation (Note 5)	T _C = +25°C	P_{D}	30	VV	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	0	57		
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{ heta JA}$	35	°C/W	
Thermal Resistance, Junction to Case (Note 5)	$R_{\theta JC}$	4.2			
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to 150	°C	

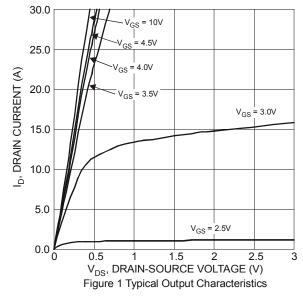
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

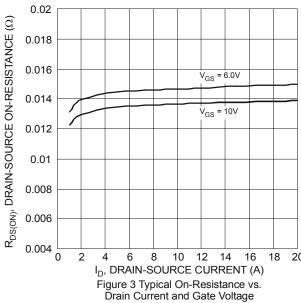
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	80		1	>	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}		_	1	μA	V _{DS} = 64V, V _{GS} = 0V	
Gate-Source Leakage			_	±100	nA	V _{GS} = ±20V, V _{DS} = 0V	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	$V_{GS(th)}$	1	1.5	3	٧	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	Б		13	16	mΩ	V _{GS} = 10V, I _D = 12A	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	14	22		V _{GS} = 6V, I _D = 6A	
Diode Forward Voltage	V_{SD}	_	0.9	1.2	V	V _{GS} = 0V, I _S = 12A	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C _{iss}		1949	_			
Output Capacitance	Coss		177	_	pF	$V_{DS} = 40V, V_{GS} = 0V,$ f = 1MHz	
Reverse Transfer Capacitance	Crss		10	_		1 - 1101112	
Gate resistance	R_g		0.7	_	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	15	_			
Total Gate Charge (V _{GS} = 10V)	Qg		34	_	~C	V _{DS} = 40V, I _D = 12A	
Gate-Source Charge	Q _{gs}	_	6	_	nC		
Gate-Drain Charge	Q _{gd}	_	4.5	_			
Turn-On Delay Time	t _{D(on)}	_	4.9	_		V_{DD} = 40V, V_{GS} = 10V, I_{D} = 12A, R_{G} = 1.6 Ω ,	
Turn-On Rise Time	t _r	_	3.8	_	0		
Turn-Off Delay Time	t _{D(off)}	_	16.5	-	nS		
Turn-Off Fall Time	t _f	_	3.5				
Body Diode Reverse Recovery Time	t _{rr}	_	30.2	_	nS	1 404 45/45 4004/	
Body Diode Reverse Recovery Charge	Qrr	_	34.6	_	nC	-I _F = 12A, di/dt = 100A/μs	

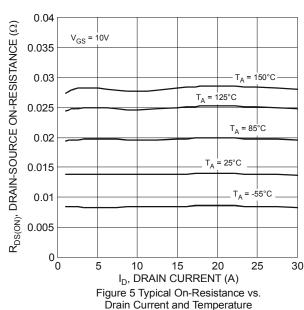
Notes:

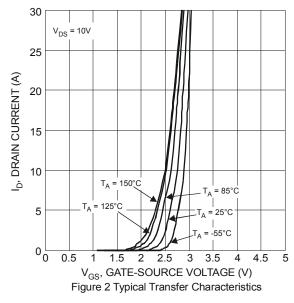
- 5. R_{0JA} is determined with the device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. R_{0JC} is guaranteed by design while R_{0JA} is determined by the user's board design.
- 6. Short duration pulse test used to minimize self-heating effect.
- 7. Guaranteed by design. Not subject to product testing.

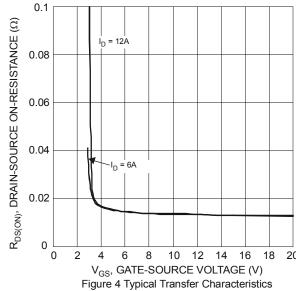












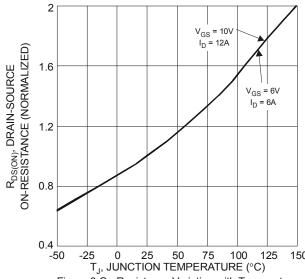
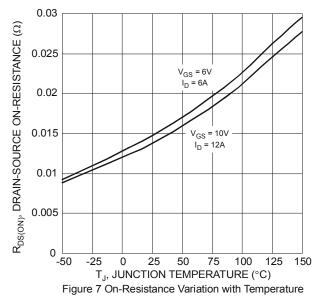
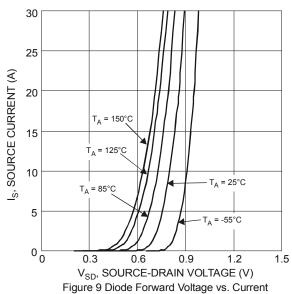
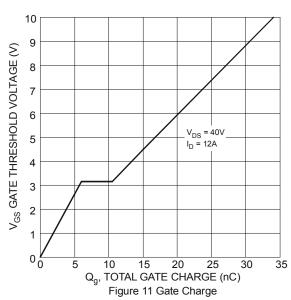


Figure 6 On-Resistance Variation with Temperature









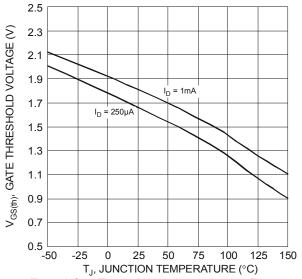
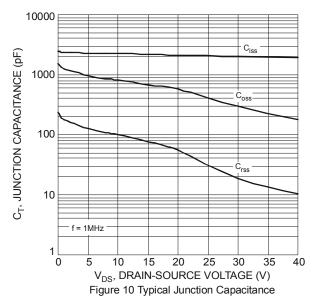
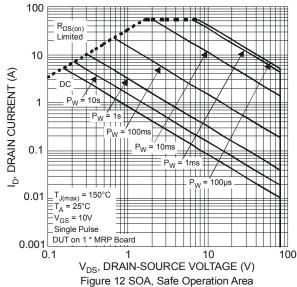
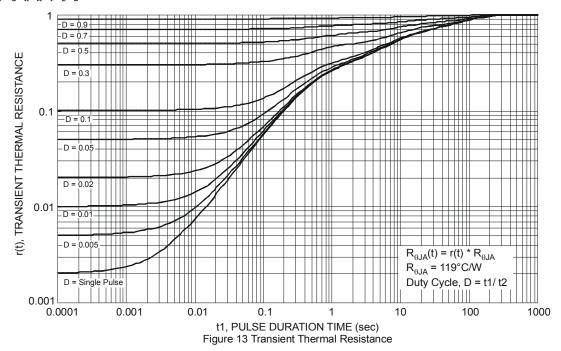


Figure 8 Gate Threshold Variation vs. Ambient Temperature



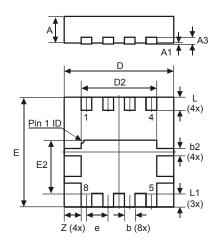






Package Outline Dimensions

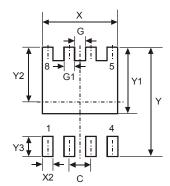
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



POWERDI®3333-8					
Dim	Min	Max	Тур		
D	3.25	3.35	3.30		
Е	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
E2	1.56	1.66	1.61		
Α	0.75	0.85	0.80		
A1	0	0.05	0.02		
A3	_	_	0.203		
b	0.27	0.37	0.32		
b2	_	_	0.20		
L	0.35	0.45	0.40		
L1	_	_	0.39		
е	_	_	0.65		
Z	_	_	0.515		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.



Dimensions	Value (in mm)				
С	0.650				
G	0.230				
G1	0.420				
Y	3.700				
Y1	2.250				
Y2	1.850				
Y3	0.700				
X	2.370				
X2	0.420				



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